	Type	Hits	Search Text	DBs
1	BRS	1877	(Trench with MOSFET) and implant$5	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
2	BRS	535	S1 and (epitaxial with silicon)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
3	BRS	2103	trench and (NPN with transistor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
4	BRS	10	S3 and S4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB

	Type	Hits	Search Text	DBs
5	BRS	6	"5763902"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM TDB
6	BRS	141	(form with trench) with after with (implant$5 with layer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM TDB
7	BRS	5	S3 and S7	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM TDB
8	BRS	188	(channel with region) with over with (drift with region)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM TDB

	Type	Hits	Search Text	DBs
9	BRS	45	S4 and trench	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM TDB
10	BRS	229	trench with (NPN with transistor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM TDB
11	BRS	0	S10 and S11	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM TDB
12	BRS	166	(forming with trench) with after with (forming with implant$5 with layer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM TDB

	Type	Hits	Search Text	DBs
13	BRS	4161	257/327,330,341.ccls. or 438/270,302,514,519,527,542,5 48.ccls.	US-PGPUB; USPAT
14	BRS	3344	S13 and implant$5	US-PGPUB; USPAT
15	BRS	1718	S14 and epitax$6	US-PGPUB; USPAT
16	BRS	390	S15 and channel and drift	US-PGPUB; USPAT
17	BRS	350	(channel and drift) with implant$5	US-PGPUB; USPAT
18	BRS	1287	(epitaxial with silicon) with doping	US-PGPUB; USPAT
19	BRS	756	S18 and channel	US-PGPUB; USPAT